

BAR63...

## Silicon PIN Diodes

- PIN diode for high speed switching of RF signals
- Very low forward resistance (low insertion loss)
- Very low capacitance (high isolation)
- For frequencies up to 3GHz
- Pb-free (RoHS compliant) package
- Qualified according AEC Q101<sup>1)</sup>



BAR63-02.. BAR63-03W

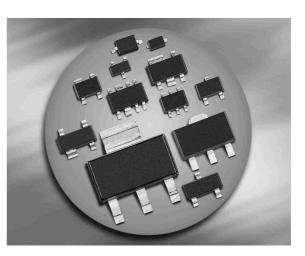
И

2

BAR63-04 BAR63-04W



BAR63-05 BAR63-05W



BAR63-06 BAR63-06W



Туре	Package	Configuration	<b>L</b> <sub>S</sub> (nH)	Marking
BAR63-02L*	TSLP-2-1	single, leadless	0.4	G
BAR63-02V	SC79	single	0.6	G
BAR63-02W	SCD80	single	0.6	GG
BAR63-03W	SOD323	single	1.8	white G
BAR63-04	SOT23	series	1.8	G4s
BAR63-04W	SOT323	series	1.4	G4s
BAR63-05	SOT23	common cathode	1.8	G5s
BAR63-05W	SOT323	common cathode	1.4	G5s
BAR63-06	SOT23	common anode	1.8	G6s
BAR63-06W	SOT323	common anode	1.4	G6s

<sup>1</sup>\*BAR63-02L is not qualified according AEC Q101



**Maximum Ratings** at  $T_A = 25^{\circ}$ C, unless otherwise specified

Parameter	Symbol	Value	Unit V	
Diode reverse voltage	V <sub>R</sub>	50		
Forward current	/ <sub>F</sub>	100	mA	
Total power dissipation	P <sub>tot</sub>		mW	
BAR63-02L, <i>T</i> <sub>S</sub> ≤ 118°C		250		
BAR63-02V, -02W, BAR63-03W, <i>T</i> <sub>S</sub> ≤ 115°C		250		
BAR63-04BAR63-06 <i>, T</i> S ≤ 55°C		250		
BAR63-04S <i>, T</i> <sub>S</sub> ≤ 115°C		250		
BAR63-04WBAR63-06W, $T_{S} \le 105^{\circ}C$		250		
Junction temperature	T <sub>i</sub>	150	°C	
Operating temperature range	T <sub>op</sub>	-55 125		
Storage temperature	T <sub>stq</sub>	-55 150		

#### **Thermal Resistance**

Parameter	Symbol	Value	Unit
Junction - soldering point <sup>1)</sup>	R <sub>thJS</sub>		K/W
BAR63-02L		≤ 125	
BAR63-02V, BAR63-02W		≤ <b>140</b>	
BAR63-03W		≤ 155	
BAR63-04BAR63-06		≤ <b>380</b>	
BAR63-04S		≤ <b>180</b>	
BAR63-04WBAR63-06W		≤ <b>180</b>	

## **Electrical Characteristics** at $T_A = 25^{\circ}$ C, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics	·	·			
Breakdown voltage	V <sub>(BR)</sub>	50	-	-	V
I <sub>(BR)</sub> = 5 μA					
Reverse current	I <sub>R</sub>	-	-	10	nA
<i>V</i> <sub>R</sub> = 35 V					
Forward voltage	V <sub>F</sub>	-	0.95	1.2	V
<i>I</i> <sub>F</sub> = 100 mA					

<sup>1</sup>For calculation of  $R_{\rm thJA}$  please refer to the Technical Information



Parameter	Symbol		Values			
		min.	typ.	max.	<u> </u>	
AC Characteristics				-		
Diode capacitance	CT				pF	
$V_{R} = 5 V, f = 1 MHz$		-	0.21	0.3		
<i>V</i> <sub>R</sub> = 0 V, 100 MHz 1.8 GHz		-	0.3	-		
Reverse parallel resistance	R <sub>P</sub>				kΩ	
V <sub>R</sub> = 0 V, <i>f</i> = 100 MHz		-	500	-		
V <sub>R</sub> = 0 V, <i>f</i> = 1 GHz		-	15	-		
V <sub>R</sub> = 0 V, <i>f</i> = 1.8 GHz		-	5	-		
Forward resistance	r <sub>f</sub>				Ω	
<i>I</i> <sub>F</sub> = 5 mA, <i>f</i> = 100 MHz		-	1.2	2		
<i>I</i> <sub>F</sub> = 10 mA, <i>f</i> = 100 MHz		-	1	-		
Charge carrier life time	τ <sub>rr</sub>	-	75	-	ns	
$I_{\rm F}$ = 10 mA, $I_{\rm R}$ = 6 mA, measured at $I_{\rm R}$ = 3 mA,						
<i>R</i> <sub>L</sub> = 100 Ω						
I-region width	W	-	4.5	-	μm	
Insertion loss <sup>1)</sup>	/L				dB	
<i>I</i> <sub>F</sub> = 1 mA, <i>f</i> = 1.8 GHz		-	0.15	-		
<i>I</i> <sub>F</sub> = 5 mA, <i>f</i> = 1.8 GHz		-	0.11	-		
<i>I</i> <sub>F</sub> = 10 mA, <i>f</i> = 1.8 GHz		-	0.1	-		
Isolation <sup>1)</sup>	I <sub>SO</sub>				1	
V <sub>R</sub> = 0 V, <i>f</i> = 0.9 GHz		-	17.9	-		
V <sub>R</sub> = 0 V, <i>f</i> = 1.8 GHz		-	12.3	-		
<i>V</i> <sub>R</sub> = 0 V, <i>f</i> = 2.45 GHz		-	10	-		
Series inductance	L <sub>S</sub>	-	-	-		

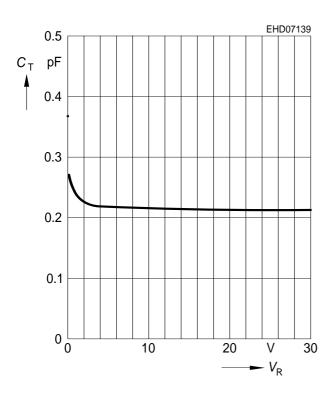
# **Electrical Characteristics** at $T_A = 25^{\circ}$ C, unless otherwise specified

<sup>1</sup>BAR63-02L in series configuration,  $Z = 50\Omega$ 



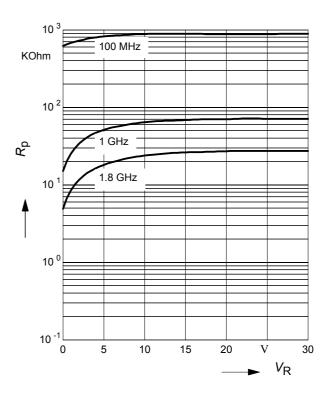
## **Diode capacitance** $C_{T} = f(V_{R})$

f = 1MHz - 1.8GHz



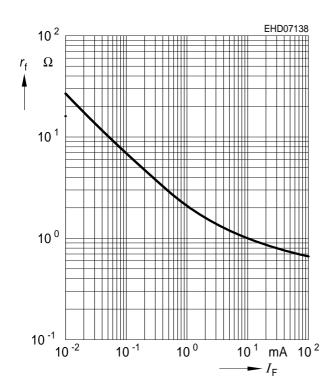
# Reverse parallel resistance $R_{\rm P}$ = $f(V_{\rm R})$

f = Parameter

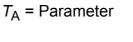


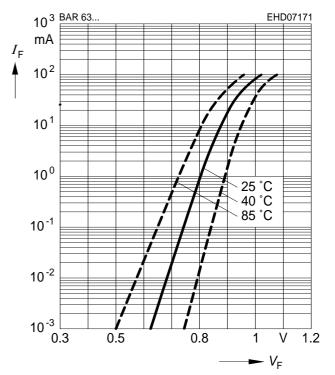
Forward resistance  $r_{\rm f} = f (I_{\rm F})$ 

*f* = 100MHz



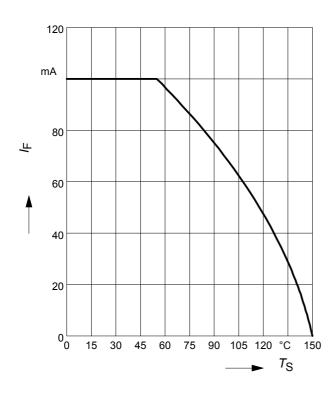
Forward current  $I_{\rm F} = f(V_{\rm F})$ 



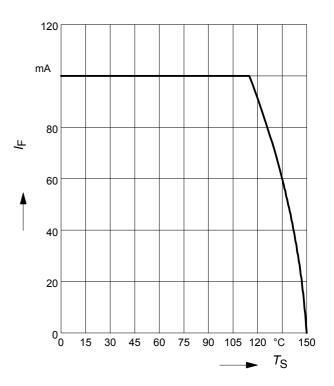




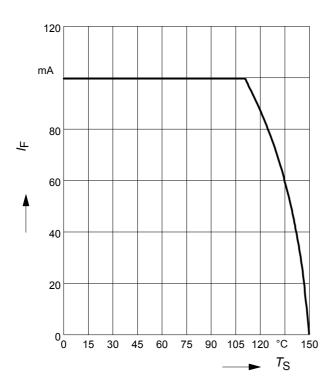
Forward current  $I_F = f(T_S)$ BAR63-04...BAR63-06



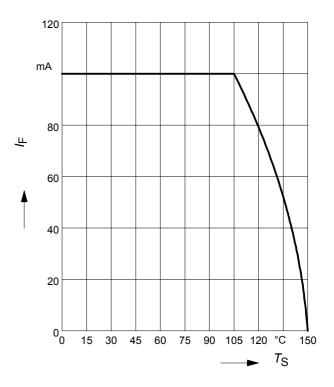
Forward current  $I_F = f(T_S)$ BAR63-02V, BAR63-02W



Forward current  $I_F = f(T_S)$ BAR63-03W



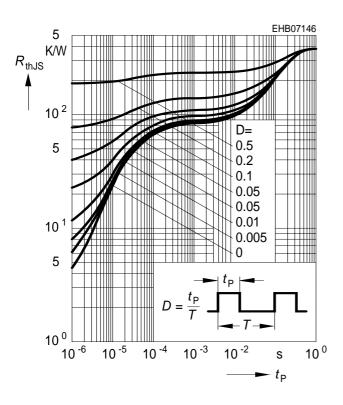
Forward current  $I_F = f(T_S)$ BAR63-04W...BAR63-06W



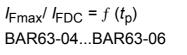


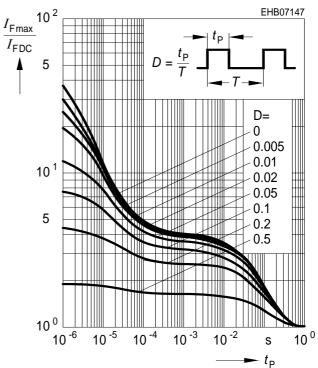
# Permissible Puls Load $R_{thJS}$ = $f(t_p)$

BAR63-04...BAR63-06

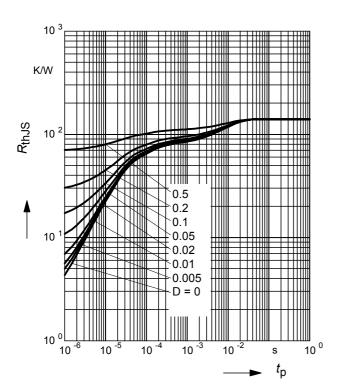


### Permissible Pulse Load



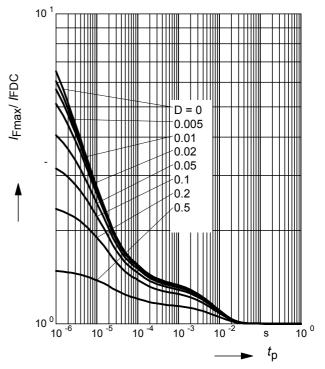


## **Permissible Puls Load** $R_{\text{thJS}} = f(t_p)$ BAR63-02V, BAR63-02W



## Permissible Pulse Load

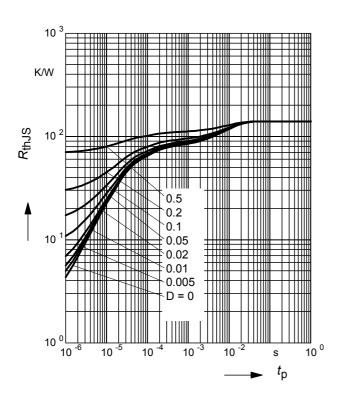
 $I_{\text{Fmax}}/I_{\text{FDC}} = f(t_{\text{p}})$ BAR63-02V, BAR63-02W



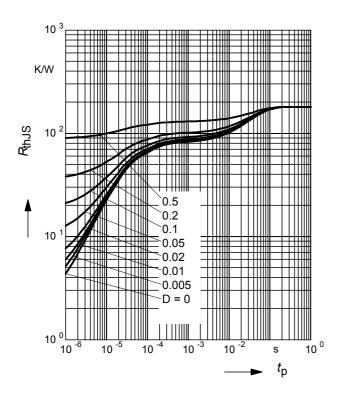


# Permissible Puls Load $R_{thJS}$ = $f(t_p)$

BAR63-03W



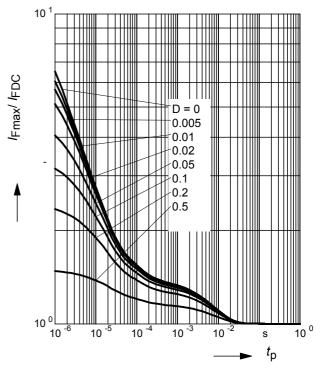
# **Permissible Puls Load** $R_{\text{thJS}} = f(t_p)$ BAR63-04W...BAR63-06W



## Permissible Pulse Load

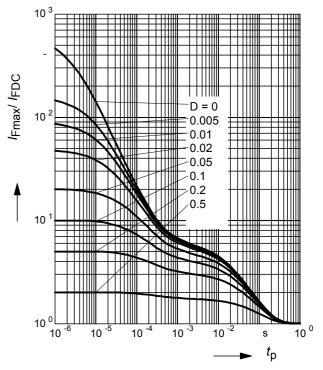
 $I_{\text{Fmax}}/I_{\text{FDC}} = f(t_{\text{p}})$ 

BAR63-03W



## Permissible Pulse Load

 $I_{\text{Fmax}}/I_{\text{FDC}} = f(t_{\text{p}})$ BAR63-04W...BAR63-06W

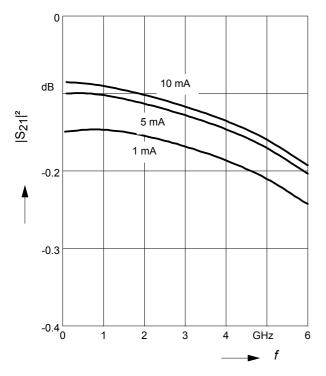




**Insertion loss**  $I_{L} = -|S_{21}|^2 = f(f)$ 

 $I_{\rm F}$  = Parameter

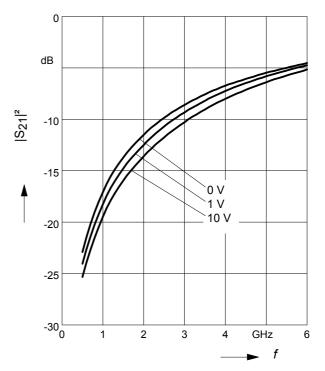
BAR63-02L in series configuration,  $Z = 50\Omega$ 



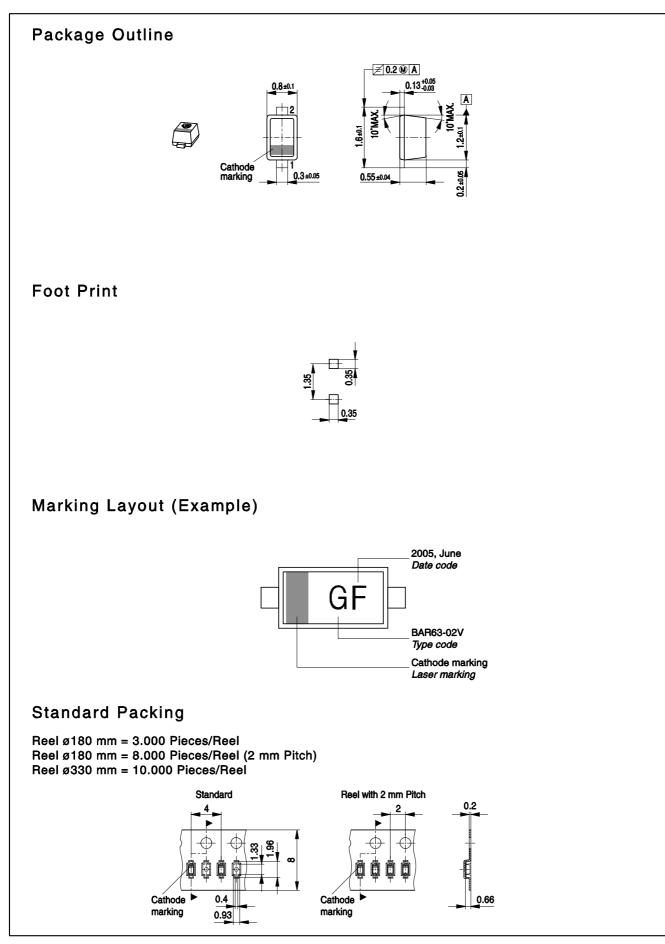
**Isolation**  $I_{SO} = -|S_{21}|^2 = f(f)$ 

 $V_{\rm R}$  = Paramter

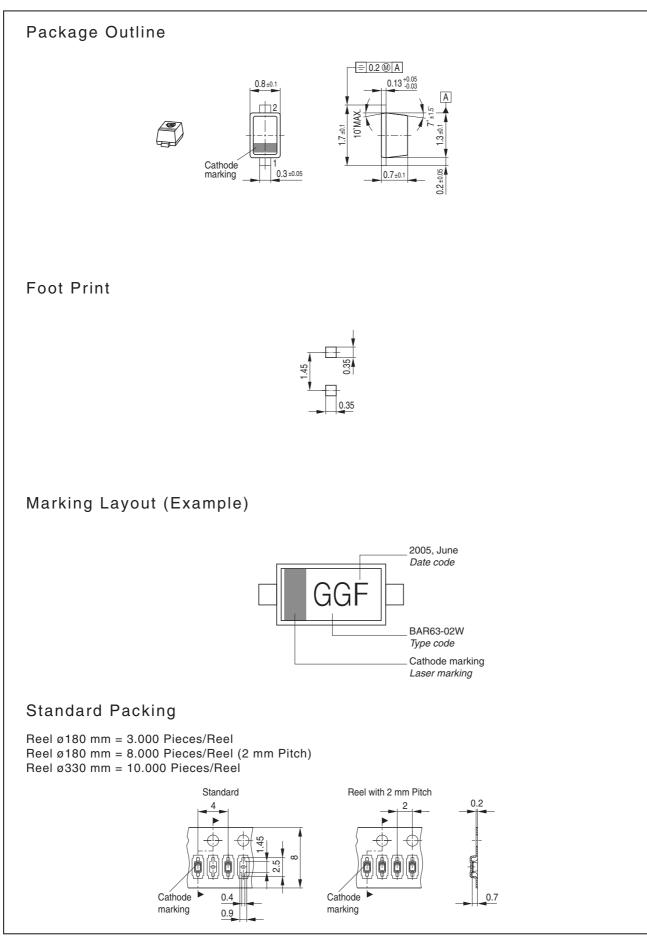
BAR63-02L in series configuration,  $Z = 50\Omega$ 











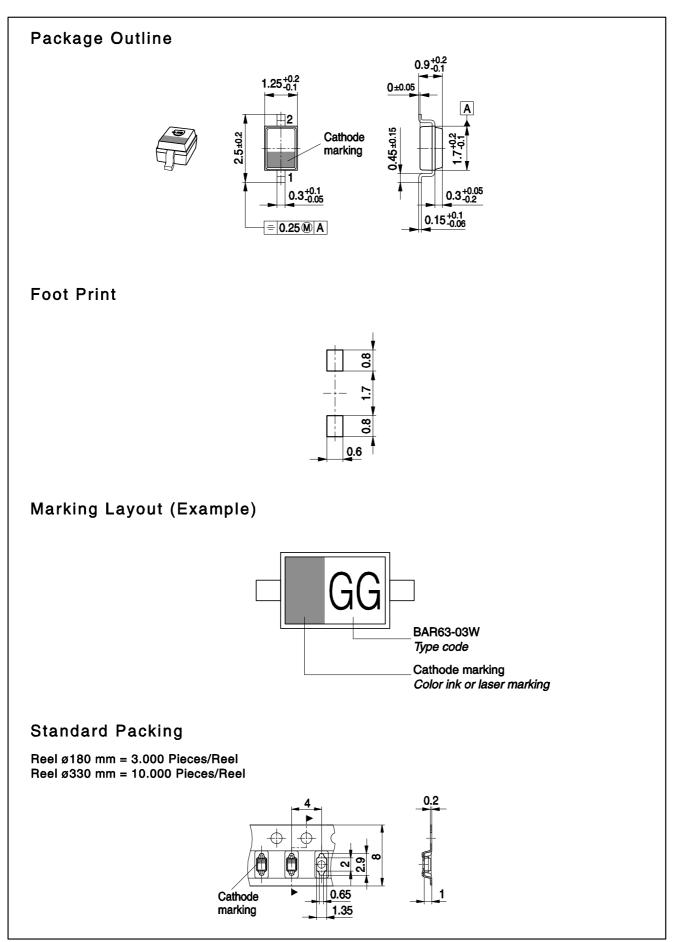


# Date Code marking for discrete packages with one digit (SCD80, SC79, SC75<sup>1)</sup>) CES-Code

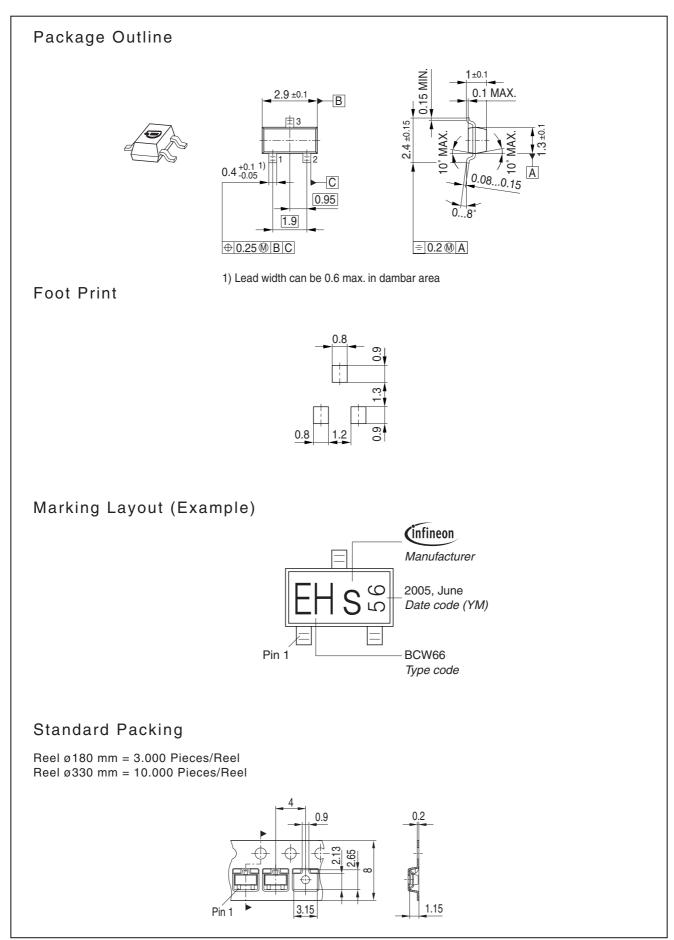
Month	2003	2004	2005	2006	2007	2008	2009	2010	2011	2012	2013	2014
01	а	р	А	Ρ	а	р	А	Р	а	р	А	Р
02	b	q	В	Q	b	q	В	Q	b	q	В	Q
03	С	r	С	R	С	r	С	R	С	r	С	R
04	d	S	D	S	d	S	D	S	d	S	D	S
05	е	t	E	Т	е	t	E	Т	е	t	Е	Т
06	f	u	F	U	f	u	F	U	f	u	F	U
07	g	V	G	V	g	V	G	V	g	V	G	V
08	h	х	Н	Х	h	х	Н	Х	h	х	Н	Х
09	j	у	J	Y	j	у	J	Y	j	у	J	Y
10	k	Z	K	Z	k	Z	K	Z	k	Z	K	Z
11	I	2	L	4	I	2	L	4	I	2	L	4
12	n	3	Ν	5	n	3	Ν	5	n	3	Ν	5

1) New Marking Layout for SC75, implemented at October 2005.

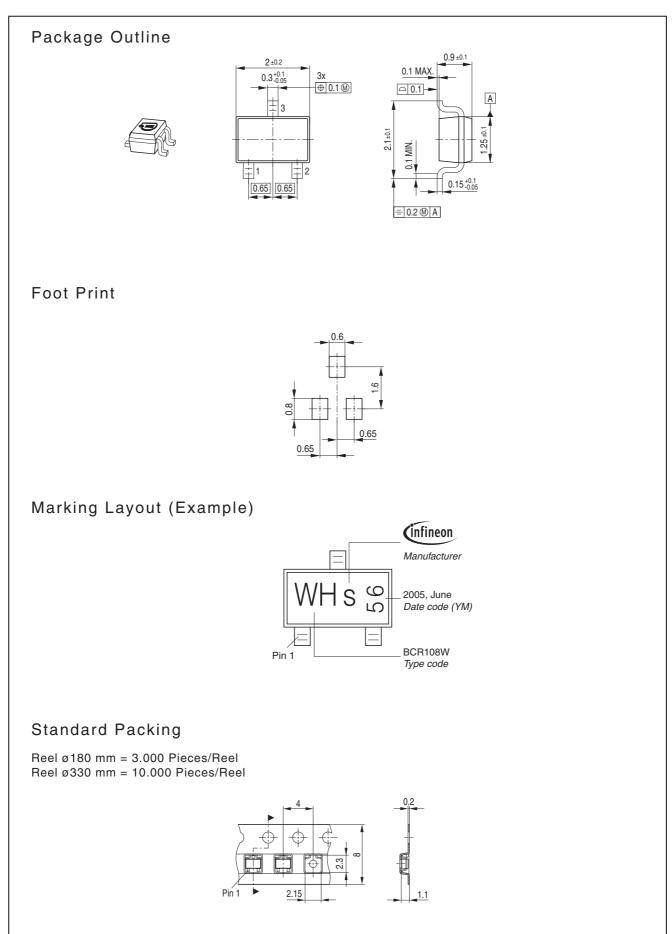




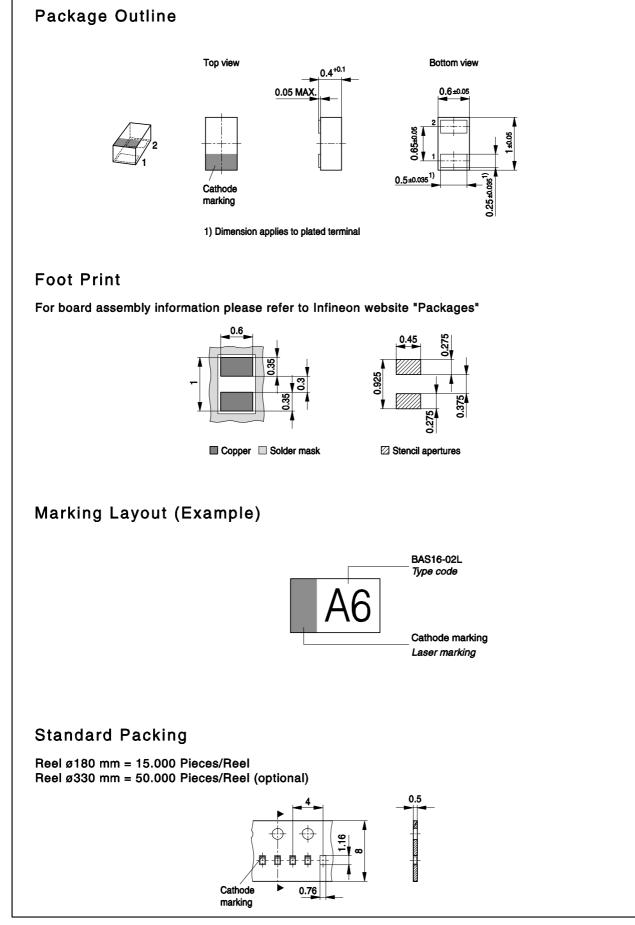
















Edition 2009-11-16

Published by Infineon Technologies AG 81726 Munich, Germany

© 2009 Infineon Technologies AG All Rights Reserved.

#### Legal Disclaimer

The information given in this document shall in no event be regarded as a guarantee of conditions or characteristics. With respect to any examples or hints given herein, any typical values stated herein and/or any information regarding the application of the device, Infineon Technologies hereby disclaims any and all warranties and liabilities of any kind, including without limitation, warranties of non-infringement of intellectual property rights of any third party.

#### Information

For further information on technology, delivery terms and conditions and prices, please contact the nearest Infineon Technologies Office (<<u>www.infineon.com</u>>).

#### Warnings

Due to technical requirements, components may contain dangerous substances. For information on the types in question, please contact the nearest Infineon Technologies Office.

Infineon Technologies components may be used in life-support devices or systems only with the express written approval of Infineon Technologies, if a failure of such components can reasonably be expected to cause the failure of that life-support device or system or to affect the safety or effectiveness of that device or system. Life support devices or systems are intended to be implanted in the human body or to support and/or maintain and sustain and/or protect human life. If they fail, it is reasonable to assume that the health of the user or other persons may be endangered.